

5th Generation CoolSiC™ 1200V Schottky Diode

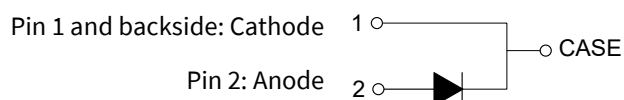
SiC Diode

Features

- No reverse recovery current / no forward recovery
- High surge current capability
- Temperature independent switching behaviour
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Specified dv/dt ruggedness
- Pb-free lead plating; RoHS compliant



Pin definition



Potential applications

- Industrial power supplies: Industrial UPS
- Infrastructure-Charge: Charger
- Metal treatment: Welding
- Solar central inverters, Solar string inverter and Solar optimizer

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

Description

- System efficiency improvement over Si diodes
- Enabling higher frequency / increased power density solutions
- System size/cost savings due to reduced heatsink requirements and smaller magnetics
- Reduced EMI
- Highest efficiency across the entire load range
- Robust diode operation during surge events
- High reliability
- Related Links: www.infineon.com/SiC



Key performance parameters

Type	V_{DC}	I_F	Q_C	$T_{vj,max}$	Marking	Package
IDWD10G120C5	1200 V	10 A	57nC	175°C	D1012C5	PG-TO247-2

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1 Maximum ratings

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage $T_C \geq 25^\circ\text{C}$	V_{RRM}	1200	V
Continuous forward current for $R_{th(j-c,max)}$ $T_C = 156^\circ\text{C}, D=1$ $T_C = 135^\circ\text{C}, D=1$ $T_C = 25^\circ\text{C}, D=1$	I_F	10 16 34	A
Surge repetitive forward current, sine halfwave ¹ $T_C=25^\circ\text{C}, t_p=10\text{ms}$ $T_C=100^\circ\text{C}, t_p=10\text{ms}$	$I_{F,RM}$	40 30	A
Surge non-repetitive forward current, sine halfwave $T_C=25^\circ\text{C}, t_p=10\text{ms}$ $T_C=150^\circ\text{C}, t_p=10\text{ms}$	$I_{F,SM}$	140 130	A
Non-repetitive peak forward current $T_C = 25^\circ\text{C}, t_p=10 \mu\text{s}$	$I_{F,max}$	1070	A
i^2t value $T_C = 25^\circ\text{C}, t_p=10 \text{ ms}$ $T_C = 150^\circ\text{C}, t_p=10 \text{ ms}$	$\int i^2 dt$	98 84	A ² s
Diode dv/dt ruggedness $V_R=0\dots960 \text{ V}$	dv/dt	150	V/ns
Power dissipation for $R_{th(j-c,max)}$ $T_C = 25^\circ\text{C}$	P_{tot}	148	W

¹ Not subject to production test. The test was performed with 20000 pulses (two consecutive half-wave rectified sines with 10 ms period).

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SiC Diode



Maximum ratings

Operating temperature	T_{vj}	-55...175	°C
Storage temperature	T_{stg}	-55...150	°C
Soldering temperature, wave soldering only allowed at leads 1.6mm (0.063 in.) from case for 10 s	T_{sld}	260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

2 Thermal resistances

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Characteristic						
Diode thermal resistance, junction – case	$R_{th(j-c)}$		-	0.8	1.0	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	leaded	-	-	62	K/W

3 Electrical Characteristics

Static Characteristics, at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
DC blocking voltage	V_{DC}	$T_{vj} = 25^{\circ}\text{C}$, $I_R = 500\mu\text{A}$	1200	-	-	V
Diode forward voltage	V_F	$I_F = 10\text{A}$, $T_{vj} = 25^{\circ}\text{C}$	-	1.4	1.65	V
		$I_F = 10\text{A}$, $T_{vj} = 150^{\circ}\text{C}$	-	1.7	-	
Reverse current	I_R	$V_R = 1200\text{V}$, $T_{vj} = 25^{\circ}\text{C}$	-	6	80	μA
		$V_R = 1200\text{V}$, $T_{vj} = 150^{\circ}\text{C}$	-	28	-	

Dynamic Characteristics, at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Total capacitive charge	Q_C	$V_R = 800\text{V}$, $T_{vj} = 150^{\circ}\text{C}$ & 25°C $Q_C = \int_0^{V_R} C(V) dV$	-	57	-	nC
Total Capacitance	C	$V_R = 1\text{V}$, $f = 1\text{MHz}$	-	730	-	pF
		$V_R = 400\text{V}$, $f = 1\text{MHz}$	-	51	-	
		$V_R = 800\text{V}$, $f = 1\text{MHz}$	-	41	-	

4 Electrical Characteristics Diagrams

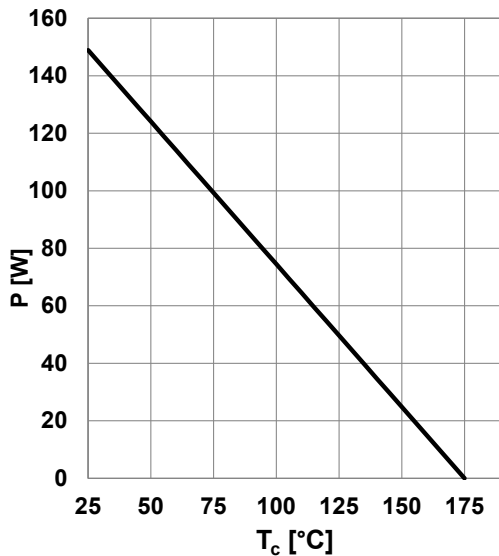


Figure 1. Power dissipation as function of case temperature, $P_{tot}=f(T_C)$, $R_{th(j-c),max}$

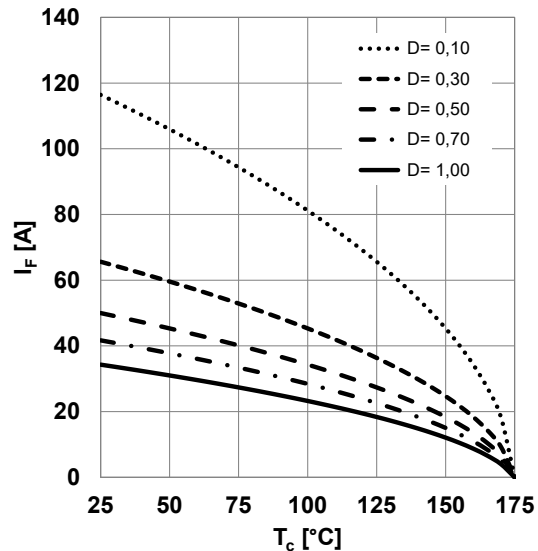


Figure 2. Diode forward current as function of temperature, parameter: $T_{vj} \leq 175^\circ\text{C}$, $R_{th(j-c),max}$, D =duty cycle, V_{th} , R_{diff} @ $T_{vj}=175^\circ\text{C}$

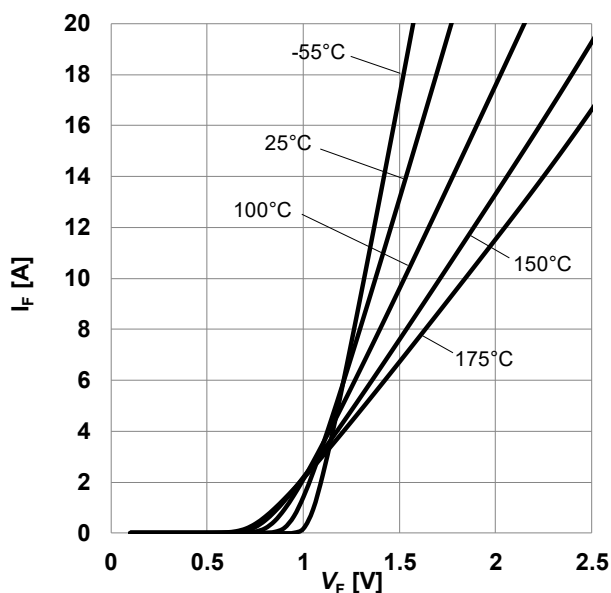


Figure 3. Typical forward characteristics, $I_F=f(V_F)$, $t_p=10\text{ }\mu\text{s}$, parameter: T_{vj}

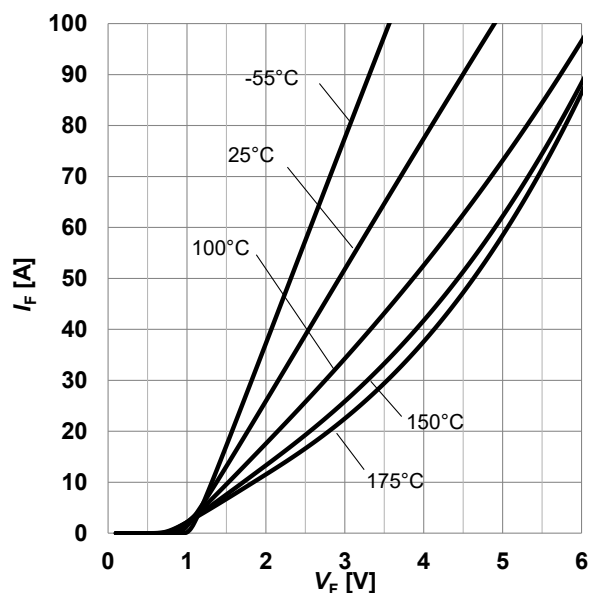


Figure 4. Typical forward characteristics in surge current, $I_F=f(V_F)$, $t_p=10\text{ }\mu\text{s}$, parameter: T_{vj}

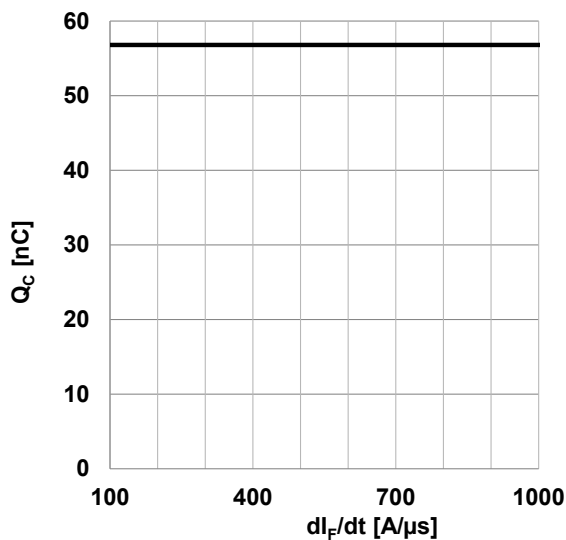


Figure 5. Typical capacitive charge as function of current slope², $Q_C=f(dI_F/dt)$, $T_{vj}=150^\circ\text{C}$

2) guaranteed by design

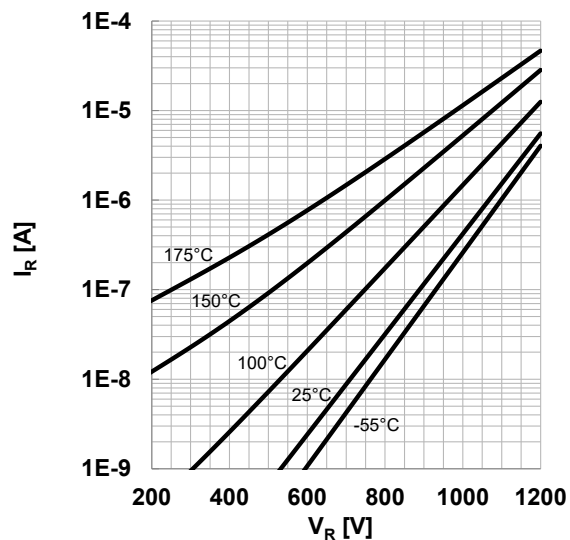


Figure 6. Typical reverse characteristics, $I_R=f(V_R)$, parameter: T_{vj}

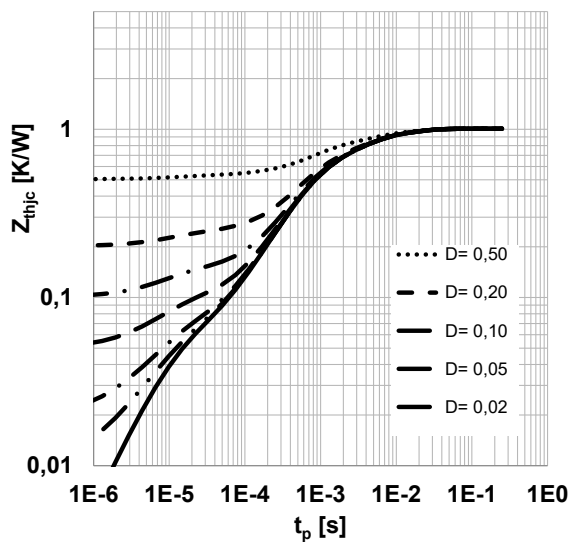


Figure 7. Max. transient thermal impedance, $Z_{th,j-c}=f(t_P)$, parameter: $D=t_P/T$

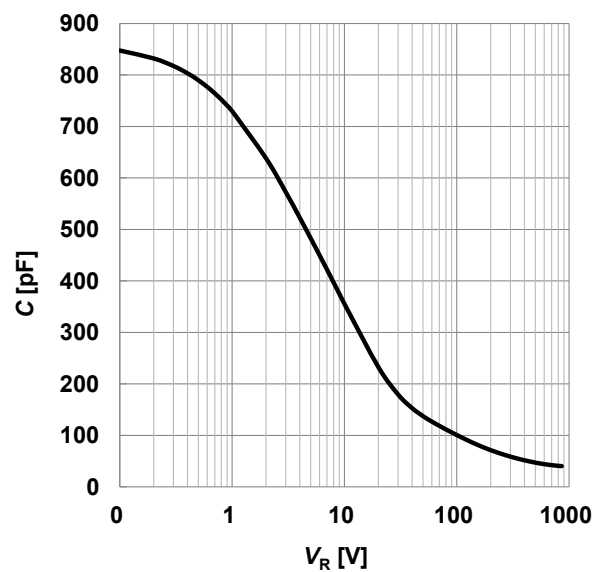


Figure 8. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_{vj}=25^\circ\text{C}$; $f=1$ MHz

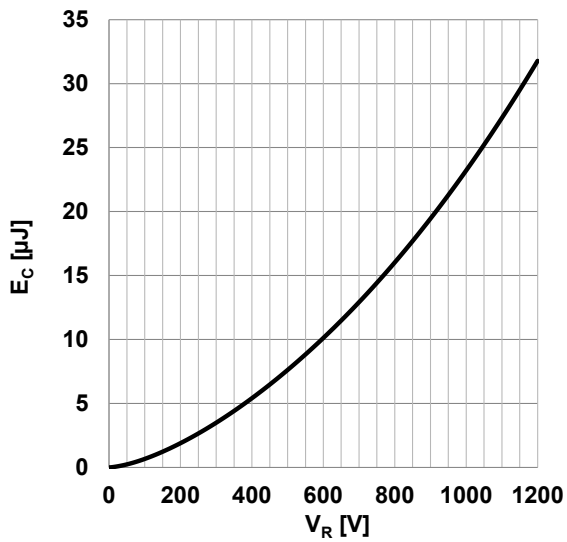
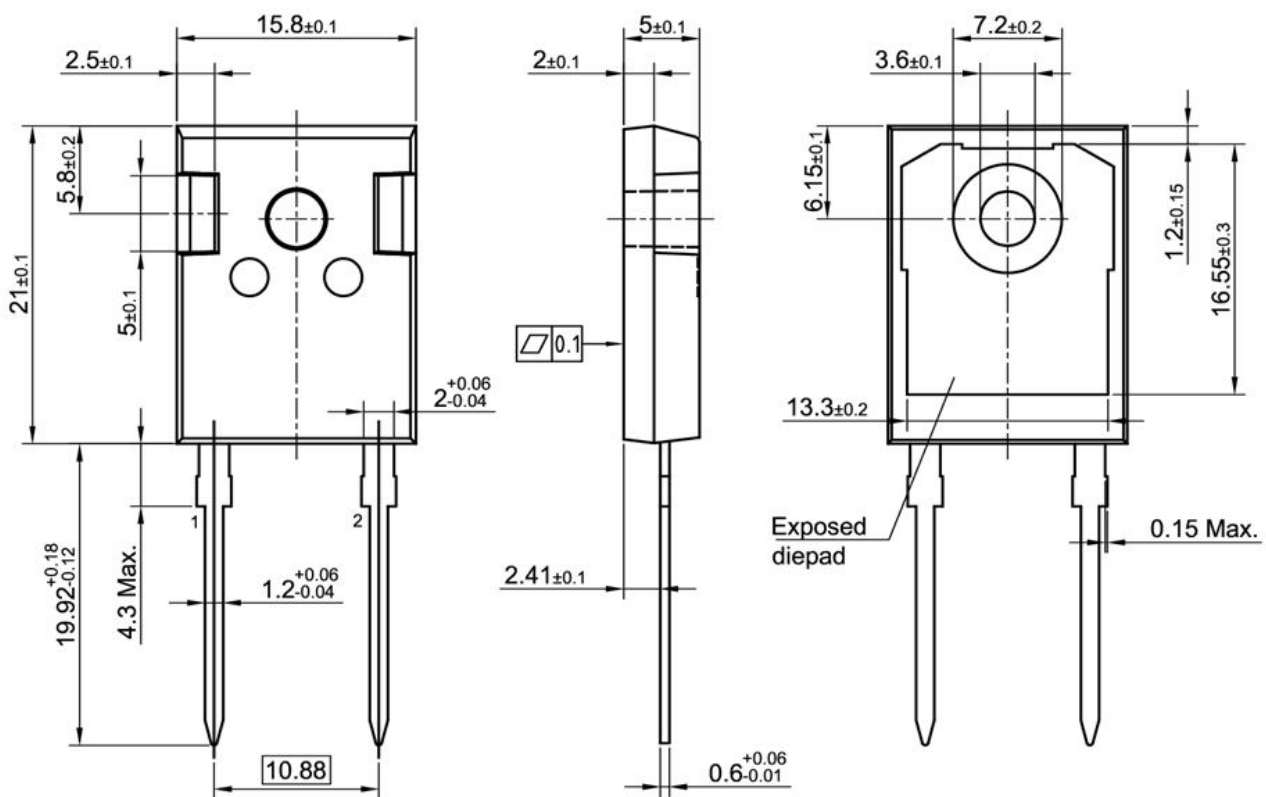


Figure 9. Typical capacitively stored energy as function of reverse voltage, $E_C=f(V_R)$

5 Package Drawing

PG-TO247-2



All dimensions do not include mold flash or protrusions

All dimensions are in units mm

The drawing is in compliance with ISO 128-30, Projection Method 1 []

Revision history

Revision history

Document version	Date of release	Description of changes
V 1.0	2018-12-21	Preliminary Datasheet
V 2.0	2019-01-30	Final Datasheet
V 2.1	2021-03-01	Increased dv/dt ruggedness

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